

L Number	Hits	Search Text		Time stamp
1	1	6255698.pn.	USPAT	2002/09/25 09:45
2	45	isolation with trench with etch with rate	USPAT	2002/09/25 09:49
3	0	isolation with trench with etch with cost	USPAT	2002/09/25 09:49
4	4	isolation with trench with etch\$5 with cost	USPAT	2002/09/25 09:50
5	17	isolation with trench with etch\$5 with improve	USPAT	2002/09/25 09:53
6	79	trench with etch\$5 with improve	USPAT	2002/09/25 10:03
7	539	trench with etch\$5 with oxidation	USPAT	2002/09/25 10:06
8	0	trench with etch\$5 with oxidation with cost	USPAT	2002/09/25 12:30
9	5	trench with etch\$5 with oxidation with improve	USPAT	2002/09/25 10:04
10	1	trench with etch\$5 with oxidation with preferable	USPAT	2002/09/25 10:06
11	115	trench with etch\$5 with commonly	USPAT	2002/09/25 10:15
12	1	4631803.pn.	USPAT	2002/09/25 10:15
13	4	("5447887" "6140688").pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/25 12:37
-	1595	(438/427).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:48
-	38	((438/427).CCLS.) and oxide and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:49
-	6	((438/427).CCLS.) and oxide and silicide) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:53
-	541	signal with line and ground with line and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 14:47
-	123	(signal with line and ground with line and 438/\$.ccls.) and barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:56
-	16	((signal with line and ground with line and 438/\$.ccls.) and barrier) and evaporation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 14:32
-	2	((signal with line and ground with line and 438/\$.ccls.) and barrier) and evaporation) and ((signal with line and ground with line and 438/\$.ccls.) and barrier) and silicide) and ((signal with line and ground with line and 438/\$.ccls.) and barrier) and silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 13:57



-	115	signal via line and ground with trench	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:15
-	75	(438/42).CCLS.		2002/09/23 15:22
-	219	(438/31).CCLS.		2002/09/23 15:30
-	7	("3616282"   "5032220"   "5121237"   "5617493"   "5834055"   "5895742"   "5959765").PN.	USPAT	2002/09/23 15:28
-	111	((438/31).CCLS.) and substrate with (trench hole via gap through )	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:39
-	1342	coplanar with waveguide	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:38
-	665	(coplanar with waveguide) and signal and ground	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:38
-	340	((coplanar with waveguide) and signal and ground) and substrate with (trench hole via gap through )	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:40
-	43	(((coplanar with waveguide) and signal and ground) and substrate with (trench hole via gap through )) and barrier	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:46
-	32	waveguide and micron.as.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:49
-	522	forbes and micron.as.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:50
-	236	forbes and ahn and micron.as.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:51
-	52	(forbes and ahn and micron.as.) and signal and ground	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:56
-	1756	waveguide and 257/\$.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/23 15:56

-	123	(waveguide and 257/\$.ccls.) and signal with ground	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:00
-	77	(369/194).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:02
-	396	coplanar with waveguide and 333/\$.ccls.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:04
-	173	coplanar with waveguide and silicon with substrate	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:22
-	46	substrate with trench and barrier and signal and ground and silicon and oxide and silane and etch	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:25
-	683	(438/653).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:49
-	421	((438/653).CCLS.) and substrate with (trench gap via cavity through hole)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:49
-	335	((438/653).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:54
-	2	((((438/653).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and ground same signal	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:55
-	302	((((438/653).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:55
-	149	((((438/653).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier) and etch	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:38
-	130	(438/665).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:58
-	52	((438/665).CCLS.) and substrate with (trench gap via cavity through hole)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:54
-	651	(438/687).CCLS.	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/23 16:53

-	411	((438/687).CCLS.) and substrate with (trench gap via cavity through hole)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:54
-	281	((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:55
-	249	((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:55
-	2	((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier) and ground same signal	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:56
-	71	((438/687).CCLS.) and substrate with (trench gap via cavity through hole)) and silicon with substrate) and barrier) and conductive with line	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:57
-	0	isolation with trench and silicon with substrate with 438/\$.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 16:59
-	5033	isolation with trench and silicon with substrate and 438/\$.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 17:00
-	39	(isolation with trench and silicon with substrate and 438/\$.ccls.) and waveguide	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 17:06
-	3602	(isolation with trench and silicon with substrate and 438/\$.ccls.) and etch	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 17:06
-	1738	(isolation with trench and silicon with substrate and 438/\$.ccls.) and etch with substrate	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 17:07
-	108	((isolation with trench and silicon with substrate and 438/\$.ccls.) and etch with substrate) and ground and signal	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/23 17:07
-	14	("4252862"   "5277985"   "5539256"   "5595937"   "5705857"   "5719447"   "5744394"   "5903053"   "5909635"   "5976986"   "6010966"   "6033986"   "6054380"   "6080529").PN.	USPAT	2002/09/23 17:43
-	5	("5516579"   "5525837"   "5607722"   "5641985"   "5659057").PN.	USPAT	2002/09/23 17:43
-	12	5903053.URPN.	USPAT	2002/09/23 17:44
-	9	("4394223"   "4810332"   "5071518"   "5132775"   "5272376"   "5298687"   "5326412"   "5382447"   "5545927").PN.	USPAT	2002/09/23 17:46
-	3	5705857.URPN.	USPAT	2002/09/23 17:46
-	9	5429978.URPN.	USPAT	2002/09/23 17:49

-	17	("489466"   "4988637"   "5026659"   "5065273"   "5214603"   "5292678"   "5336629"   "5343354"   "5348905"   "5378907"   "5384277"   "5389559"   "5395786"   "5429978"   "5661057"   "5670805"   "5753526").PN.	USPAT	2002/09/24 09:52
-	0	copper with isolation with trench and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/25 12:31
-	5	("5208175"   "5372963"   "5534455"   "5547884"   "5589412").PN.	USPAT	2002/09/24 09:54
-	7	copper with isolation with trench and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/24 09:57
-	7	copper with gate same isolation with trench and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/24 09:58
-	11	5909044.URPN.	USPAT	2002/09/24 09:57
-	1	copper with ground and isolation with trench and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/24 10:00
-	3	copper with line same isolation with trench and 438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/25 12:37
-	360	waveguide with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2002/09/24 10:02
-	174	waveguide with trench	USPAT	2002/09/24 10:17
-	3	("3425879"   "5094973"   "5104824").PN.	USPAT	2002/09/24 10:14
-	1	5783844.URPN.	USPAT	2002/09/24 10:14
-	58	waveguide and trench and barrier and oxide and copper	USPAT	2002/09/24 10:26
-	106	silicon with substrate and oxide with substrate and barrier with oxide and barrier with metal and metal with copper and etch and silicide	USPAT	2002/09/24 10:29
-	35	(silicon with substrate and oxide with substrate and barrier with oxide and barrier with metal and metal with copper and etch and silicide) and trench	USPAT	2002/09/24 11:11
-	2	gate with polysilicon with copper same high with temperature	USPAT	2002/09/24 11:14
-	0	gate with polysilicon with copper with cost	USPAT	2002/09/24 11:13
-	0	gate with polysilicon with copper with improve	USPAT	2002/09/24 11:13
-	98	gate with polysilicon with copper	USPAT	2002/09/24 11:52
-	2648	silicide with silicon with nitride	USPAT	2002/09/24 11:54
-	1399	silicide with silicon with nitride and 438/\$.cccls.	USPAT	2002/09/24 11:55
-	705	silicide with silicon with nitride and 438/6\$2.cccls.	USPAT	2002/09/24 12:04

-	0	silicide with spacer with copper with gate	USPAT	2002/09/24 12:05
-	2	silicide with spacer with copper	USPAT	2002/09/24 13:21
-	0	silicide with copper and sinane	USPAT	2002/09/24 13:22
-	176	silicide with copper and silane	USPAT	2002/09/24 13:22
-	5	silicide with copper and silane and copper with evaporation	USPAT	2002/09/24 13:24
-	20	copper with silicide and 438/655.ccls.	USPAT	2002/09/24 13:26
-	30	copper with silicide with nitride with adhesion	USPAT	2002/09/24 13:29
-	1	5,447,887.pn.	USPAT	2002/09/24 13:34
-	1	6255698.pn.	USPAT	2002/09/24 14:08
-	312	thermal with evaporation with CVD	USPAT	2002/09/24 14:09
-	104	thermal with evaporation with CVD and 438/\$.ccls.	USPAT	2002/09/24 14:11
-	35	thermal with thermal adj evaporation with CVD and 438/\$.ccls.	USPAT	2002/09/24 14:11
-	35	thermal adj evaporation with CVD and 438/\$.ccls.	USPAT	2002/09/24 14:15
-	0	thermal adj evaporation with CVD with (cost improve)	USPAT	2002/09/25 09:41